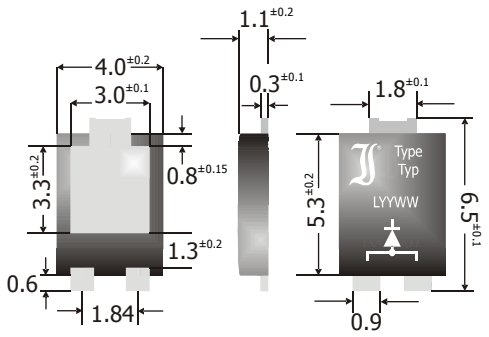
PPS560, PPS5100

Surface Mount Schottky Rectifier Diodes
Schottky-Gleichrichterdioden für die Oberflächenmontage

Version 2014-08-21



Dimensions - Maße [mm]

Nominal Current Nennstrom	5 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung	60...100 V
Plastic case Kunststoffgehäuse	PowerSMD
Weight approx. Gewicht ca.	0.1 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging taped and reeled Standard Lieferform gegurtet auf Rolle	

RoHS Pb WEEE ELV

Green Molding
Halogen-Free

Features / **Vorteile**

Compatible to industry standard packages — Kompatibel zu industrieüblichen Gehäusen

Tentative Entwurf

Maximum ratings and Characteristics / **Grenz- und Kennwerte**

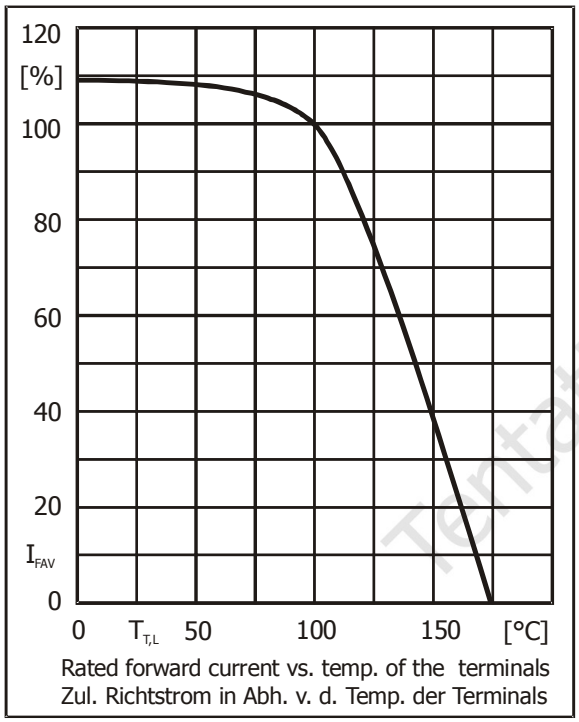
Type Typ	Repet. / Surge peak rever. voltage Periodische- / Spitzen-Sperrspg. V_{RRM} [V] / V_{RSM} [V]	Forward Voltage Durchlass-Spannung V_F [V] T_j = 125°C [1])		Forward Voltage Durchlass-Spannung V_F [V] T_j = 25°C [1])	
		I_F = 2 A	I_F = 5 A	I_F = 2 A	I_F = 5 A
PPS560	60	tbd	tbd	< tbd	< 0.69
PPS5100	100	tbd	tbd	< tbd	< 0.88

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	T_C = 100°C	I_{FAV}	20A [2])
Repetitive peak forward current Periodischer Spitzenstrom	f > 15 Hz	I_{FRM}	30 A [2])
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwelle	T_A = 25°C	I_{FSM}	150/165 A [2])
Rating for fusing, t < 10 ms Grenzlastintegral, t < 10 ms	T_A = 25°C	i^2t	112 A^2s [2])
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-50...+150°C -50...+150°C

1 Both anode pins connected – Beide Anodenanschlüsse kontaktiert

Characteristics **Kennwerte**

Leakage current Sperrstrom	PPS560	T_j = 25°C T_j = 125°C	$V_R = V_{RRM}$ $V_R = V_{RRM}$ $V_R = V_{RRM}$	I_R I_R I_R	typ. tbd µA < 150 µA typ. tbd mA
Leakage current Sperrstrom	PPS5100	T_j = 25°C T_j = 125°C	$V_R = V_{RRM}$ $V_R = V_{RRM}$ $V_R = V_{RRM}$	I_R I_R I_R	typ. tbd µA < 15 µA typ. tbd mA
Thermal resistance junction to case Wärmewiderstand Sperrschicht - Gehäuse				R_{thC}	< 2.0 K/W
Typical Junction Capacitance Typische Sperrschichtkapazität			V_R = 4 V	C_j	200 pF



Rated forward current vs. temp. of the terminals
Zul. Richtstrom in Abh. v. d. Temp. der Terminals

Tentative
Entwurf

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